## Integrated IEEE 802.3af **PoE-PD Interface Controller**

### NCP1090, NCP1091, **NCP1092**

#### Description

The NCP1090, NCP1091 and NCP1092 are members of ON Semiconductor's high power HIPO<sup>™</sup> Power over Ethernet Powered Device (PoE-PD) product family and integrate an IEEE 802.3af PoE-PD interface controller.

The 3 variants all incorporate the required functions as such detection, classification, under voltage lockout, inrush and operational current limit. A power good signal has been added to guarantee a good enabling/disabling of the DC-DC controller. In addition, the NCP1091 offers a programmable under-voltage while the NCP1092 provide an auxiliary pin for applications supporting auxiliary supplies.

The NCP1090, NCP1091 and NCP1092 are fabricated in a robust high voltage process and integrates a rugged vertical N-channel DMOS suitable for the most demanding environments and capable of withstanding harsh environments such as hot swap and cable ESD events.

The NCP1090, NCP1091 and NCP1092 complement Solutions to the x.
Solutions to the x.
A y
Programmable Classification Current
Adjustable Under Voltage Lock Out (NCP1091 Only)
Open-Drain Power Good Indicator
130 mA Inrush Current Limit
500 mA Operational Current
Pass Switch Principle ON Semiconductor's ASSP portfolio in industrial devices and can be

- (NCP1092 Only)
- Over-temperature Protection
- Industrial Temperature Range -40°C to 85°C with Full Operation up to 125°C Junction Temperature
- 0.5 Ω Hot–swap Pass–switch
- Vertical N-channel DMOS Pass-switch Offers the Robustness of Discrete MOSFETs

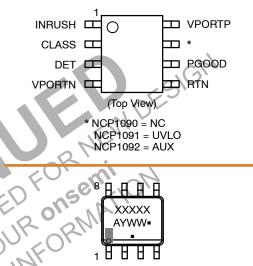




SOIC-8 **S SUFFIX** CASE 751AZ

TSSOP-8 **T SUFFIX CASE 948S** 





XXXXXX = Specific Device Code

= Assembly Location

= Year

WW

= Work Week

= Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCP109xxxx	SOIC-8 (Pb-Free)	2500/Tape & Reel
NCP109xxxx	TSSOP-8 (Pb-Free)	2500/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

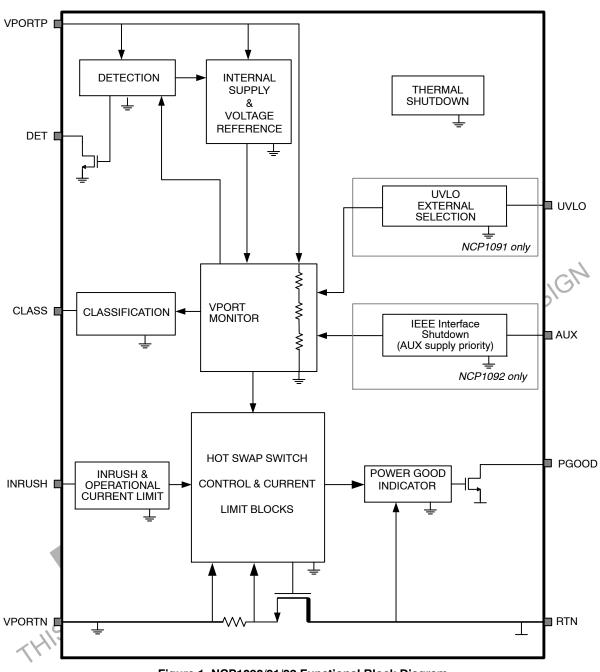
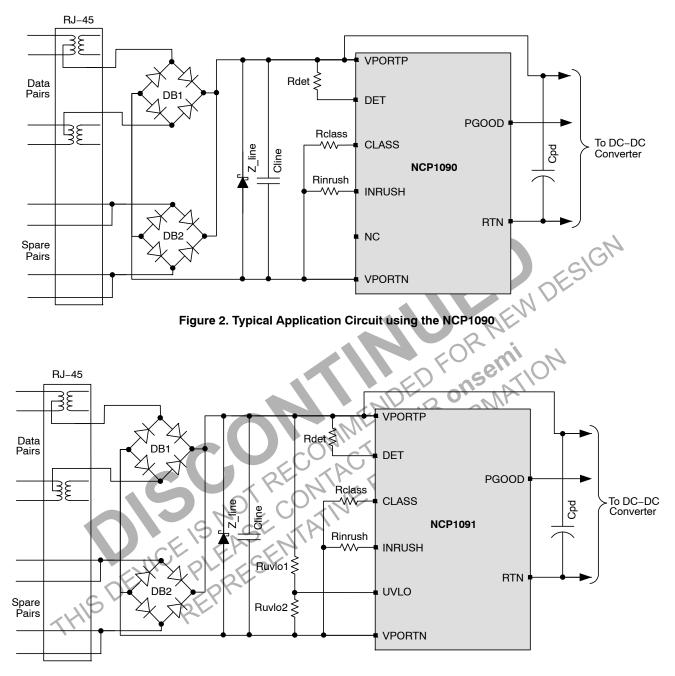
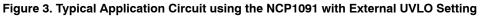


Figure 1. NCP1090/91/92 Functional Block Diagram

#### SIMPLIFIED APPLICATION DIAGRAMS





#### **Table 1. PIN DESCRIPTION**

		Pin No.				
Name	NCP1090	NCP1091	NCP1092	Туре	Description	
INRUSH	1	1	1	Output	Current limit programming pin. Connect a resistor between INRUSH and VPORTN.	
CLASS	2	2	2	Output	Classification current programming pin. Connect a resistor between CLASS and VPORTN.	
DET	3	3	3	Output, Open Drain	Detection pin. Connect a 24.9 $k\Omega$ resistor between DET and VPORTP for a valid PD detection signature.	
VPORTN	4	4	4	Ground	Negative input power. Connected to the source of the internal pass-switch	
RTN	5	5	5	Ground	DC-DC controller power return. Connected to the drain of the internal pass-switch	
PGOOD	6	6	6	Output, Open Drain	Open Drain Power Good Indicator. Pin is in HZ mode when the power good signal is active.	
NC	7	-	-	-	No connection	
UVLO	-	7	-	Input	Under-voltage lockout input, Voltage with respect to VPORTN. Connect a resistor-divider from VPORTP to UVLO to VPORTNx to set an external UVLO threshold.	
AUX	-	-	7	Input	Auxiliary Pin. When this pin is pulled up, the Pass Switch is disabled and allows a supply transition from PSE to the rear auxiliary supply connected between VPORTP and RTN.	
VPORTP	8	8	8	Input	Positive input power. Voltage with respect to VPORTN.	
DPERATING CONDITIONS Table 2. ABSOLUTE MAXIMUM RATINGS						

#### **OPERATING CONDITIONS**

#### Table 2. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Min	Мах	Units	Conditions
VPORTP	Input power supply	-0.3	72	V	Voltage with respect to VPORTN
RTN	Analog ground supply 2	-0.3	72	~~	Pass-switch in off-state (voltage with respect to VPORTN)
CLASS	Analog output	-0.3	72	v	Voltage with respect to VPORTN
INRUSH	Analog output	-0.3	3.6		Voltage with respect to VPORTN
AUX	Analog input	-0.3	72	V	Voltage with respect to VPORTN
UVLO	Analog input	-0.3	3.6	V	Voltage with respect to VPORTN
PGOOD	Analog output	-0.3	72	V	Voltage with respect to RTN
Та	Ambient temperature	-40	85	°C	
Tj	Junction temperature	_	125	°C	
Tj-TSD	Junction temperature (Note 1)	-	175	°C	Thermal shutdown condition
T <sub>stg</sub>	Storage Temperature	-55	150	°C	
ΤθJA	Thermal Resistance, Junction to Air (Note 2)	150 160	240 260	°C/W	SOIC-8 TSSOP-8
ESD-HBM	Human Body Model	2		kV	per EIA-JESD22-A114 standard
ESD-CDM	Charged Device Model	500		V	per ESD-STM5.3.1 standard
ESD-MM	Machine Model	200		V	per EIA-JESD22-A115-A standard
LU	Latch-up	±100		mA	per JEDEC Standard JESD78

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tj-TSD allowed during error conditions only. It is assumed that this maximum temperature condition does not occur more than 1 hour cumulative during the useful life for reliability reasons.

Low θJA is obtained with 2S2P test board (2 signal – 2 plane). High θJA is obtained with double sideboard with minimum pad area and natural convection. Refer to Jedec JESD51 for details.

#### **Recommended Operating Conditions**

Operating conditions define the limits for functional operation and parametric characteristics of the device. Note that the functionality of the device outside the operating conditions described in this section is not warranted. Operating outside the recommended operating conditions for extended periods of time may affect device reliability.

Table 3. OPERATING CONDITIONS	(All values are with res	pect to VPORTN unless otherwise noted.)

Symbol	Parameter	Min	Тур	Max	Units	Conditions
INPUT SUPPLY						
VPORT	Input supply voltage	0		57	V	VPORT = VPORTP - VPORTN
SIGNATURE DE	TECTION					
Offset_det1	I <sub>(VPORTP)</sub> + I <sub>(RTN)</sub>		2	5	μΑ	VPORTP = RTN = 1.9 V Rdet = 24.9 KΩ
Sleep_det1	I <sub>(VPORTP)</sub> + I <sub>(RTN)</sub>		15	21	μΑ	VPORTP = RTN = 9.8 V Rdet = 24.9 K $\Omega$
Offset_det2	I(VPORTP) + I(RTN) + I(DET)	73	77	81	μΑ	VPORTP = RTN = 1.9 V Rdet = 24.9 KΩ
Sleep_det2	I <sub>(VPORTP)</sub> + I <sub>(RTN)</sub> + I <sub>(DET)</sub>	390	400	412	μΑ	VPORTP = RTN = 9.8 V Rdet = 24.9 KΩ
CLASSIFICATIO	N					
Vcl_on	Classification current turn-on lower threshold	9.8	11.3	13	RVN	VPORTP rising
Vcl_off	Classification current turn-off upper threshold	21		24	ver	VPORTP rising
Vclass_reg	Classification buffer output voltage		9.8	20	K	13 V < VPORTP < 21 V
Icl_bias	I(vportp) quiescent current during classification		600	JULE (	μA	l(class) excluded 13 V < VPORTP < 21 V
Iclass0	Class 0: Rclass 4420 Ω (Note 3)			4	mA	13 V < VPORTP < 21 V
Iclass1	Class 1: Rclass 953 Ω (Note 3)	.9	ZO	12	mA	13 V < VPORTP < 21 V
Iclass2	Class 2: Rclass 549 Ω (Note 3)	17	E -	20	mA	13 V < VPORTP < 21 V
Iclass3	Class 3: Rclass 357 $\Omega$ (Note 3)	-26	-	30	mA	13 V < VPORTP < 21 V
Iclass4	Class 4: Rclass 255 $\Omega$ (Note 3)	36	-	44	mA	13 V < VPORTP < 21 V
UVLO – INTERN	AL SETTING - NCP1090/91/92					
Vuvlo_on	Default turn on voltage	-	37	40	V	VPORTP rising
Vuvlo_off	Default turn off voltage	29.6	31	-	V	VPORTP falling
Vhyst_int	UVLO internal hysteresis	-	6	-	V	
Uvlo_filter	UVLO On / Off filter time	_	100	-	μS	For information only
UVLO – EXTERN	IAL SETTING – NCP1091 ONLY					
Vuvlo_pr	UVLO external programming range	25	-	50	V	VPORTP rising
Vuvlo_on2	External UVLO turn on voltage	1.14	1.2	1.26	V	
Vhyst_off2	External UVLO turn off voltage	0.95	1	1.05	V	
Uvlo_ipd	UVLO internal pull down current	-	2.5	_	μA	
AUXILIARY SUP	PLY SETTING – NCP1092 ONLY					
Aux_h	AUX input high level voltage	3.1	-		V	
Aux_I	AUX input low level voltage	-	-	0.6	V	
Aux_pd	AUX internal pull down resistor	100	-	-	KΩ	For information only

3. A tolerance of 1% on the Rclass resistor is included in the min/max values.

Symbol	Parameter	Min	Тур	Max	Units	Conditions
PASS-SWITCH A	AND CURRENT LIMITING	-		-		
Ron	Pass-switch Rds-on	-	0.5	1	Ω	Measured with I(RTN) = 200 mA
l_inrush	Inrush current with Rinrush = 95.3 k $\Omega$	75	120	170	mA	Measured at RTN-VPORTN = 3 V
l_ilim	Operating current limit with Rinrush = $178 \text{ k}\Omega$	425	500	575	mA	Current limit threshold
POWER GOOD II	NDICATOR			-		
Vds_pgood_on	RTN-VPORTN threshold voltage required for power good status	0.8	1	1.2	V	RTN-VPORTN falling
Vds_pgood_off	RTN-VPORTN latchoff threshold voltage	9	10	11	V	RTN-VPORTN rising
Pgood_filter	PGOOD filter time		100		μS	Rising and falling / for information only
Ipgood	I(PGOOD) sinking current	-	-	5	mA	4.5
Vpgood_low	PGOOD voltage output low	_	0.2	0.5	V	Voltage with respect to RTN
CURRENT CONS	SUMPTION					
lvportP	I(VPORTP) internal current consumption	-	600	900	μA	VPORTP = 48 V
THERMAL SHUT	DOWN			OK.	cel.	
TSD	Thermal shutdown threshold	150			€С тј	Tj = junction temperature
Thyst	Thermal hysteresis	-	15		ି (ମି	Tj = junction temperature
THERMAL RATIN	IGS	11	11-10	) K	5	
Та	Ambient temperature	-40		85	°C	
Tj	Junction temperature	$\checkmark \checkmark \triangleright$	$\gamma_{z}$	125	°C	

3. A tolerance of 1% on the Relass resistor is included in the min/max values.

#### **DESCRIPTION OF OPERATION**

#### Powered Device Interface

The integrated PD interface supports the IEEE 802.3af defined operating modes: detection signature, current source classification, undervoltage lockout, inrush and operating current limits. The following sections give an overview of these previous processes.

#### Detection

During the detection phase, the incremental equivalent resistance seen by the PSE through the cable must be in the IEEE 802.3af standard specification range (23.70 k $\Omega$  to 26.30 k $\Omega$ ) for a PSE voltage from 2.7 V to 10.1 V. In order to compensate for the non–linear effect of the diode bridge and satisfy the specification at low PSE voltage, the NCP1090/91/92 present a suitable impedance in parallel with the 24.9 k $\Omega$  Rdet external resistor. For some types of diodes (especially Schottky diodes), it may be necessary to adjust this external resistor.

The Rdet resistor has to be inserted between VPORTP and DET pins. During the detection phase, the DET pin is pulled to ground and goes in high impedance mode (open-drain) once the device exit this mode, reducing thus the current consumption on the cable.

#### Classification

Once the PSE device has detected the PD device, the classification process begins. In classification, the PD regulates a constant current source that is set by the external resistor RCLASS value on the CLASS pin. Figure 4 shows the schematic overview of the classification block. The current source is defined as:

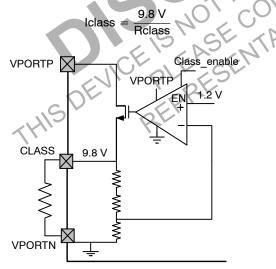


Figure 4. Classification Block Diagram

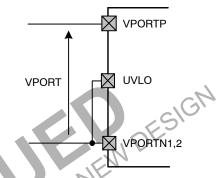
#### **Power Mode**

When the classification hand-shake is completed, the PSE and PD devices move into the operating mode.

#### Under Voltage Lock Out (UVLO)

The NCP1090/91/92 incorporate a fixed under voltage lock out (ULVO) circuit which monitors the input voltage and determines when to turn on the pass switch and charge the dc–dc converter input capacitor before the power up of the application.

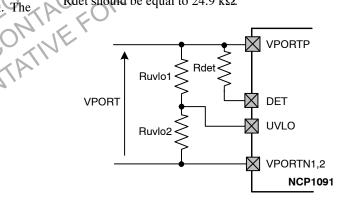
The NCP1091 offers a fixed or adjustable Vuvlo\_on threshold depending if the UVLO pin is used or not. In Figure 5, the UVLO pin is strapped to ground and the Vuvlo\_on threshold is defined by the internal level.



## Figure 5. Default Internal UVLO Configuration (NCP1091 only)

To define the UVLO threshold externally, the ULVO pin must be connected to the center of an external resistor divider between VPORTP and VPORTN as shown in Figure 6.

In order to guarantee the detection signature, the equivalent input resistor made of the Ruvlo1, Ruvlo2 and Rdet should be equal to  $24.9 \text{ k}\Omega$ .



## Figure 6. Default Internal UVLO Configuration (NCP1091 only)

For a Vuvlo\_on desired turn-on voltage threshold, Ruvlo1 and Ruvlo2 can be calculated using the following equations:

$$Ruvlo = \frac{24.9 \text{ k} \cdot \text{Rdet}}{\text{Rdet} - 24.9 \text{ k}}$$

 $Ruvlo2 = \frac{1.2}{Vuvlo on} \cdot Ruvlo$ 

with Ruvlo1 + Ruvlo2 = Ruvlo

and

With:

Vuvlo\_on: Desired Turn-On voltage threshold

#### Example for a Targeted Uvlo\_on of 35 V:

Let's start with a Rdet of  $30.1 \text{ k}\Omega$  This gives a Ruvlo of 144 k $\Omega$  made with a Ruvlo2 of 4.99 k $\Omega$  and a Ruvlo1 of 140 k $\Omega$  (closest values from E96 series). Note that there is a pull down current of 2.5  $\mu$ A typ on the UVLO. Assuming the previous example, this pull down current will create a (non critical) systematic offset of 350 mV on the Uvlon\_on level of 35 V.

The external UVLO hysteresis on the NCP1091 is about 15 percent typical.

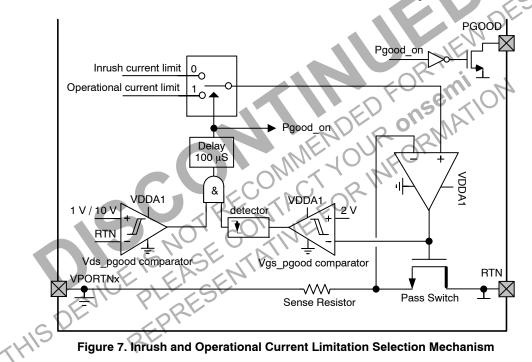
#### Inrush and Operational Current Limitations

Both inrush and operational current limit are defined by an external Rinrush resistor connected between INRUSH and VPORTN. The low inrush current limit allows smooth charge of large dc–dc converter input capacitor by limiting the power dissipation over the internal pass switch. In power mode, the operational current limit protects the pass switch and the PD application against excessive transient current and failure on the dc-dc converter output.

Once the input supply reached the Vulvo\_on level, the charge of Cpd capacitor starts with a current limitation set to to the INRUSH level. When this capacitor is fully charged, the current limit switches without any spikes from the inrush current to the operational current level and the power good indicator on PGOOD pin is turned on. The capacitor is considered to be fully charged once the following conditions are satisfied:

- 1. The drain-source voltage of the Pass Switch has decreased below the *Vds\_pgood\_on* level (typical 1 V)
- 2. The gate–source voltage of the Pass Switch is sufficiently high (above 2 V typical) which means the current in the pass switch has decreased below the current limit.

This mechanism is depicted in the following Figure 7.



The operational current limit and the power good indicator stays active as long as RTN voltage stays below the vds\_pgood\_off threshold (10 V typical) and the input supply stay above the Vulvo\_off level. Therefore, fast and large voltage step lower than 10 V are tolerated on the input without interruption of the converter controller. Higher input transient will not affect the behavior if RTN does not exceed 10 V for more than 100  $\mu$ S. Such input voltage steps may be introduced by a PSE which is switched to a higher power supply. In case RTN is still above 10 V after this delay, the power good is turned off and the pass switch current limit falls back to the inrush level.

#### **PGOOD Indicator**

The NCP1090/91/92 integrate a Power Good indicator circuitry indicating the end of the dc–dc converter input capacitor charge, and the enabling of the operational current limit. This indicator is implemented on the PGOOD pin which goes in open drain state when active and which is pulled to ground during turn off.

A possible usage of this PGOOD pin is illustrated in Figure 8. During the inrush phase, the converter controller is forced in standby mode due to the PGOOD pin forcing low the under voltage lock out pin of the controller. Once the Cpd capacitor is fully charged, PGOOD goes in open drain state, allowing the start up sequence of the converter controller.

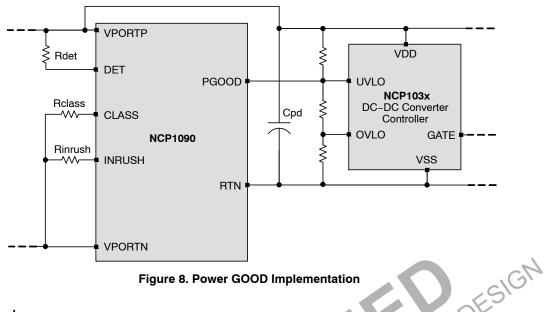


Figure 8. Power GOOD Implementation

#### **Auxiliary Supply**

To support application connected to non-PoE enabled networks and minimize the bill of materials, the NCP1093 supports drawing power from an external supply and allows simplified designs with PoE or auxiliary supply priorities.

In most of the cases, the auxiliary supply is connected between VPORTP and RTN with a serial diode between VPORTP and VAUX, as shown in Figure 9.

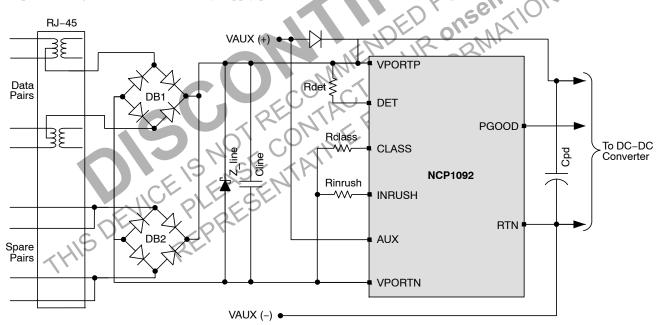


Figure 9. Auxiliary Supply Dominant PD Interface

The NCP1092 offers an AUX input pin which turns off the pass switch when pulled high. This feature is useful for PD applications where the auxiliary supply has to be dominant over the PoE supply. When the auxiliary supply is inserted on a POE powered application, the pass switch disconnection will move the current path from the PSE to the rear auxiliary supply. Since the current delivered by the PSE will goes below the DC MPS level (specified in IEEE 802.3 af/at standard), the PSE will disconnect the PoE-PD

and the application will remain supplied by the auxiliary supply. The transition will happens without any power conversion interruption since the PGOOD indicator stays active (high impedance state).

Next Figure 10 depicts an other PD application where the POE supply is dominant over the VAUX supply. A diode D1 has been added in order to not corrupt the PD detection signature when the dc-dc converter is supplied by VAUX.

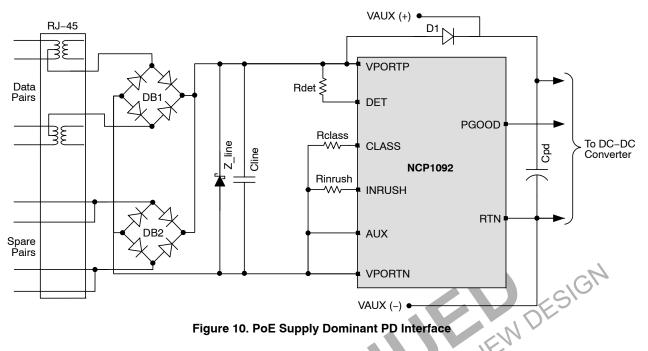


Figure 10. PoE Supply Dominant PD Interface

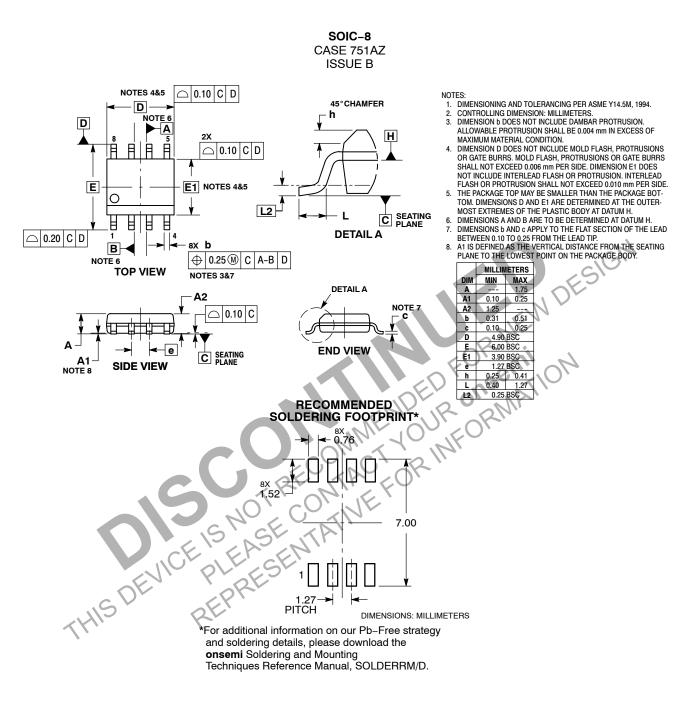
#### Thermal Shutdown

The NCP1090/91/92 include a thermal shutdown which protect the device in case of high junction temperature. Once the thermal shutdown (TSD) threshold is exceeded, the classification block, the pass switch and the PGOOD indicator are disabled. The NCP109X returns automatically to normal operation once the die temperature has fallen below the TSD low limit.

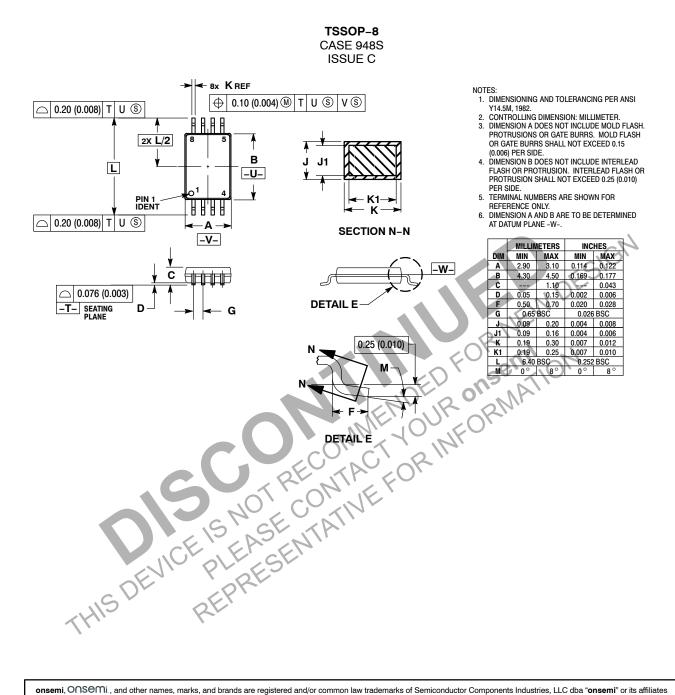
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#### PACKAGE DIMENSIONS



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#### ADDITIONAL INFORMATION

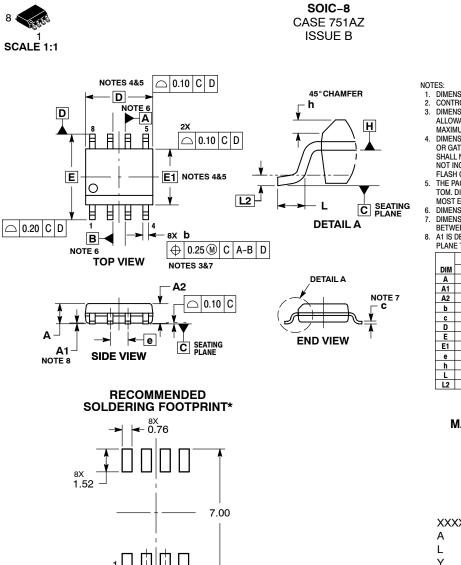
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DIMENSIONS: MILLIMETERS

#### DATE 18 MAY 2015

- IES: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.004 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- MAXIMUM MATEHIAL CONDITION. DIMENSION D DOES NOT ITICLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.006 mm PER SIDE. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD
- NOT INCLUDE INTERLEAD FLASH OF PHOTHOSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.010 mm PER SIDE. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOT-TOM. DIMENSIONS D AND E1 ARE DETERMINED AT THE OUTER-MOST EXTREMES OF THE PLASTIC BODY AT DATUM H. DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM H.
- DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 TO 0.25 FROM THE LEAD TIP.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

	MILLIMETERS					
DIM	MIN MAX					
Α		1.75				
A1	0.10	0.25				
A2	1.25					
b	0.31	0.51				
C	0.10	0.25				
D	4.90 BSC					
Е	6.00 BSC					
E1	3.90 BSC					
е	1.27	1.27 BSC				
h	0.25					
L	0.40					
L2	0.25	BSC				

GENERIC **MARKING DIAGRAM\*** 



XXXXX = Specific Device Code

- = Assembly Location
- = Wafer Lot
- = Year
- W = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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PITCH

Techniques Reference Manual, SOLDERRM/D.

\*For additional information on our Pb-Free strategy and soldering

details, please download the onsemi Soldering and Mounting

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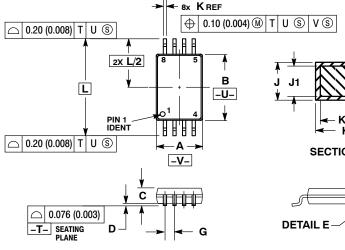


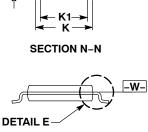
TSSOP-8 3.0x4.4x1.1 CASE 948S

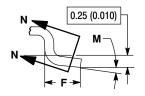
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ISSUE C







DETAIL E

NOTES:

- IOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010)

PER SIDE. 5. TERMINAL NUMBERS ARE SHOWN FOR

REFERENCE ONLY. DIMENSION A AND B ARE TO BE DETERMINED 6. AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
С		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65	BSC	0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	
М	0 °	8°	0°	8 °

#### GENERIC **MARKING DIAGRAM\***

0	XXX
	YWW
	A•
	-

XXX	= Specific Device Code
А	= Assembly Location
Y	= Year
WW	= Work Week
	= Pb-Free Package

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "∎", may or may not be present. Some products may not follow the Generic Marking.

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